PACS: 73.40Qv, 73.21As

# Influence of heat treatment on lateral lifetime charge carrier and its homogeneity in *n*-type silicon wafers

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*Received June 01, 2022*

***It is shown, that heat treatment Czochralski silicon wafers (Cz-Si) in oxygen and nitrogen ambient at 1150 $^{o}$C during initial part of device processing sequence increase in homogeneity of the lateral lifetime charge carrier distribution over wafer. The reason this results is forming denuded zone with low oxygen concentration at wafer surfaces during heat treatment, where oxygen precipitates growth is suppressed.***

*Keywords*: carrier lifetime, oxygen precipitates, diffusion of boron and phosphorus.

DOI: 10.51368/1996-0948-2022-3-43-48

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